

### GBJ20005 - GBJ2010/G

**Mechanical Data** 

Single Phase 20Amp Glass passivated Bridge Rectifiers

### **Features**

- · Glass passivated die construction
- · Low forward voltage drop
- · High current capability
- · High surge current capability
- Plastic material-UL flammability 94V-0
- The G suffix is uses for photoresist chip, otherwise it is a knife scraping chip

### **MECHANICAL DATA**

· Case: Molded plastic, GBJ

• Terminals: Plated Leads Solderable perMIL-STD-202, Method 208

· Polarity: As Marked on Case

Mounting Position: AnyMarking: Type Number

· Lead Free: For RoHS / Lead Free Version

# 1.Output Anode(+) GBJ 2.Input pin(~) 3.Input pin(~) 4.Output Cathode(-)

### Maximum Ratings And Electrical Characteristics (@T<sub>A</sub>=25°C unless otherwise noted)

		CDI CDI CDI CDI CDI CDI					CBI		
Symbol	Parameter	GBJ	GBJ	GBJ	GBJ	GBJ	GBJ	GBJ	Unit
		20005	2001	2002	2004	2006	2008	2010	
$V_{RRM}$	repetitive peak reverse voltage	50	100	200	400	600	800	1000	
$V_{RWM}$	Working Peak Reverse Voltage	50         100         200         400         600         800           35         70         140         280         420         560		1000	V				
$V_{RMS}$	RMS voltage			700					
V <sub>DC</sub>	DC blocking voltage	50	100	200	400	600	800	1000	
IF <sub>AV</sub>	Average Rectified Output	20.0							А
	Current (Note 1)@T <sub>C</sub> =90°C	20.0							
I <sub>FSM</sub>	Peak forward surge current, 8.3ms single	240						А	
	half sine-wave								
I <sub>t</sub> <sup>2</sup>	I <sub>t</sub> <sup>2</sup> Rating for fusing (t<8.3ms)	239.04					A <sub>S</sub> <sup>2</sup>		
$V_{FM}$	Forward Voltage @IF=10A	1.0						V	
	per element @IF=20A	1.10							
	Peak Reverse Current@T <sub>A</sub> =25°C	5.0						uA	
I <sub>R</sub>	at rated DC blocking voltage @T <sub>A</sub> =125°C	500							
CJ	Typical junction capacitance	65			pF				
$R_{\theta JA}$	Between junction and ambient, Without heatsink	22				°C/W			
R <sub>θJC</sub>	Between junction and case, With heatsink	1.1							
TJ	Operation Temperature Range	-55 to +150					°C		
T <sub>STG</sub>	Storage Temperature Range	-55 to +150							

Note:(1)Thermal resistance from junction to case per element. Unit mounted on 75x75x1.6mm aluminum plate heat sink. **BORN SEMICONDUCTOR**, **INC. ALL** 

Revision: 2022-Jan-1





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### **Ratings And Characteristic Curves**

Figure 1: Output Current Derating Curve

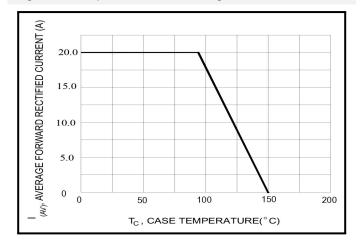


Figure 2: Typical Forward Characteristics (per leg)

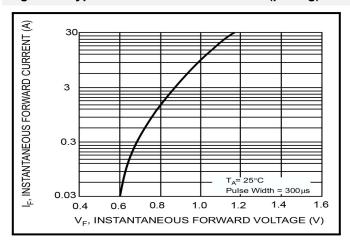
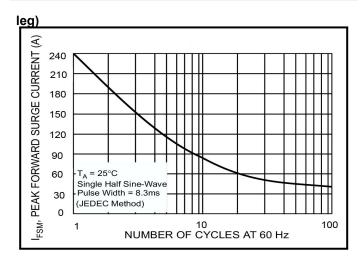


Figure 3:Maximum Peak Forward Surge Current (per



**Figure 4:Typical Junction Capacitance** 

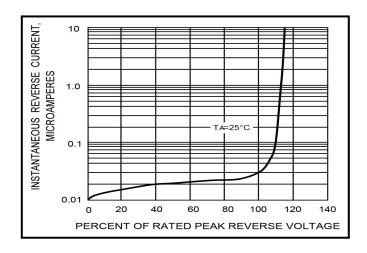
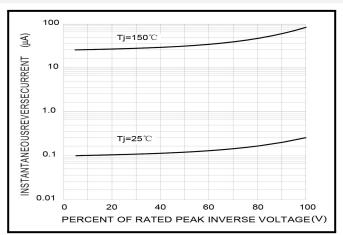


Figure 5:TYPICAL REVERSE CHARACTERISTICS



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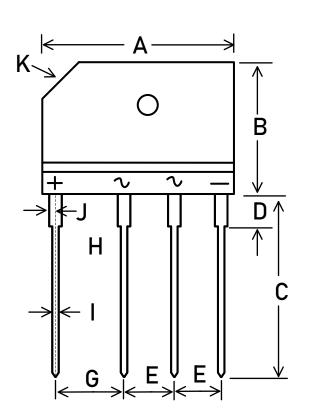


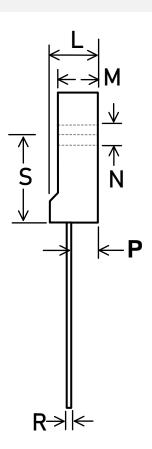


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## **Outline Drawing -GBJ**





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SYMBOL	MILLIMETER							
STWIDOL	MIN.	MAX.						
Α	29.70	30.3						
В	19.70	20.3						
С	17.00	18.00						
D	3.80	4.20						
Е	7.30	7.70						
G	9.80	10.20						
Н	2.00	2.40						
I	0.90	1.10						
J	2.30	2.70						
K	3.0x45°							
L	4.40	4.80						
М	3.40	3.80						
N	3.10	3.40						
Р	2.50	2.90						
R	0.60	0.80						
S	10.80	11.20						